Symbol	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	180	
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	107	Α

I_{DM} Pulsed Drain Current 5.12 Tf1 0 0

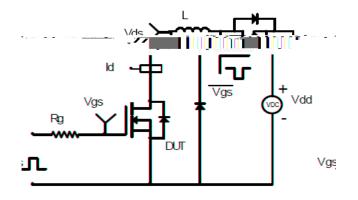


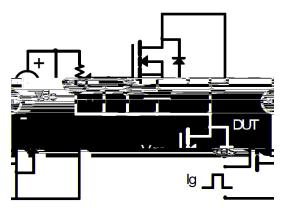
Symbol	Characterizes	Тур.	Max.	Units
	Junction-to-case			

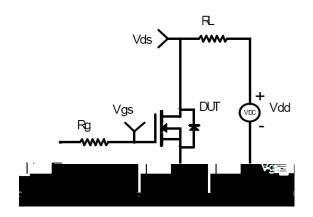
Symbol	Parameter	Min.	Тур.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	40			V	$V_{GS} = 0V, I_D$
R _{DS(on)}	Static Drain-to-Source on-resistance		1.6	3	m	$V_{GS} = 10V, I_D = 40A$
$V_{GS(th)}$	Gate threshold voltage	2		4	V	$V_{DS} = V_{GS}, I_{D}$
I _{DSS}	Drain-to-Source leakage current			1		$V_{DS} = 40V, V_{GS} = 0V$
	Cata to Source forward looked			100	nA	V _{GS} =20V
I _{GSS} Ga	Gate-to-Source forward leakage			-100		V _{GS} = -20V
C _{iss}	Input capacitance		10547			$V_{GS} = 0V$
Coss	Output capacitance		654		pF	$V_{DS} = 30V$
C _{rss}	Reverse transfer capacitance		553			1MHz
Qg	Total gate charge					I _D = 20A,
Q _{gs}	Gate-to-Source charge				nC	V _{DS} =20V,
Q_{gd}	Gate-to-Drain("Miller") charge					V _{GS} = 10V
t _{d(on)}	Turn-on delay time					
t _r	Rise time					$V_{GS}=10V, V_{DD}=20V,$
t _{d(off)}	Turn-Off delay time				ns $R_{GEN}=3.6$ $L=1$	

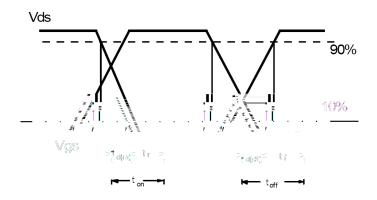
t_f Fall time









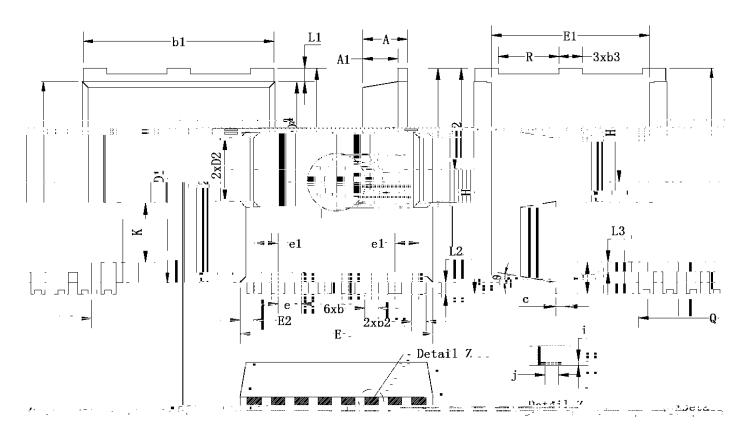


Calculated continuous current based on maximum allowable junction temperature.

Repetitive rating; pulse width limited by max. junction temperature.

The power dissipation P_D is based on max. junction temperature, using junction-to-case thermal resistance.





Symbol	Min	Typ	Max	Symbo	ol Min	Typ	Max
A	, 2.25	2.30	7.35	, F2	0.65.	0.70	0.75.
11.80	A1	1.75	1.80	1.85	III	11.60	11.70
	ь	0.65	0.70	0.75	UI		6.95 BSC
	b1	9.75	9.80	9.85	1012.		5.90 BSC
	b2.	0.70	0.75	0.80	i		0.10 REF
	www.h2		1.20,	1.25	or sessed	an Settle an	v salblur
	3.10 REF		C	0.45	0.50	0.55	K
155	1 65	1.75		10.35	10 40	.10.45	J
75	101	11.00	11.10	11.20	Li	0.65	0.70
('0. =	10 Mars - 17-17	- 3 -855	- 2.30.,	. 10 <u>10 A A A A A A A A A A A A A A A A A A A</u>	erest (1800	- 200 - 300	
Constitution of the	27. 29 1.1	0.40	Signed and	200 <u>40 jyy</u> aasa	Section 1	. A 6'0 ₅ , ₃₂	$z \in \mathcal{A}^{0} \times \frac{k^{2} k^{2} \ldots z}{2^{d-1} + z \in \mathcal{I}} = z \in \mathbb{R}$
	C		1.20 BSC		Q		7.95 RHF
9 1 K .= L L J -	1	<u></u> .	- 13 00K 10KM	No.	<u> </u>	208.	
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			11/1	200	810	2 20	معادين والاستان



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